PATENT 81788.0026

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Seiichi MORI

Serial No: 09,456,873

Filed:

December 8, 1999

For: NON-VOLATILE SEMICONDUCTOR

MEMORY DEVICE

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office, Fax No. 703 308 7722 on March

8, 2002

Art Unit: 2826

Examiner: Andujar, L.

Steron R. Mason, Reg. No 41,179

Johnson

March 8, 2002 Date

## PRELIMINARY AMENDMENT

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Prior to the examination of the above-identified application, please enter the following amendments and remarks

IN THE CLAIMS:

Rewrite claim 1 as follows:

FAX COPY RECEIVED

MAR 8 - 2002

TECHNOLOGY CENTER 2800

A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate;

wherein said inter-layer insulating layer includes:

a silicon oxide layer contiguous to said floating gate;